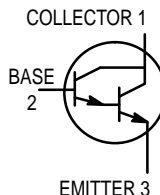


Darlington Transistors

NPN Silicon

BC517



CASE 29-04, STYLE 17
TO-92 (TO-226AA)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CES}	30	Vdc
Collector–Base Voltage	V_{CB}	40	Vdc
Emitter–Base Voltage	V_{EB}	10	Vdc
Collector Current — Continuous	I_C	1.0	Adc
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 12	mW mW/ $^\circ\text{C}$
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ($I_C = 2.0 \text{ mAdc}, V_{BE} = 0$)	$V_{(BR)CES}$	30	—	—	Vdc
Collector–Base Breakdown Voltage ($I_C = 10 \mu\text{Adc}, I_E = 0$)	$V_{(BR)CBO}$	40	—	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 100 \text{ nAdc}, I_C = 0$)	$V_{(BR)EBO}$	10	—	—	Vdc
Collector Cutoff Current ($V_{CE} = 30 \text{ Vdc}$)	I_{CES}	—	—	500	nAdc
Collector Cutoff Current ($V_{CB} = 30 \text{ Vdc}, I_E = 0$)	I_{CBO}	—	—	100	nAdc
Emitter Cutoff Current ($V_{EB} = 10 \text{ Vdc}, I_C = 0$)	I_{EBO}	—	—	100	nAdc



BC517

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS(1)					
DC Current Gain ($I_C = 20\text{ mA}$, $V_{CE} = 2.0\text{ Vdc}$)	h_{FE}	30,000	—	—	—
Collector–Emitter Saturation Voltage ($I_C = 100\text{ mA}$, $I_B = 0.1\text{ mA}$)	$V_{CE(sat)}$	—	—	1.0	Vdc
Base–Emitter On Voltage ($I_C = 10\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$)	$V_{BE(on)}$	—	—	1.4	Vdc

SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ⁽²⁾ ($I_C = 10\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	—	200	—	MHz
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1. Pulse Test: Pulse Width $\leq 2.0\%$.
2. $f_T = |h_{fe}| \cdot f_{test}$

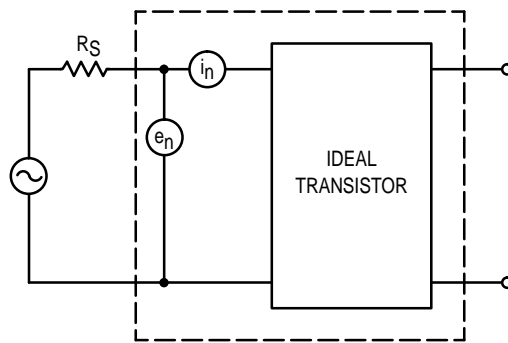


Figure 1. Transistor Noise Model

NOISE CHARACTERISTICS

($V_{CE} = 5.0 \text{ Vdc}$, $T_A = 25^\circ\text{C}$)

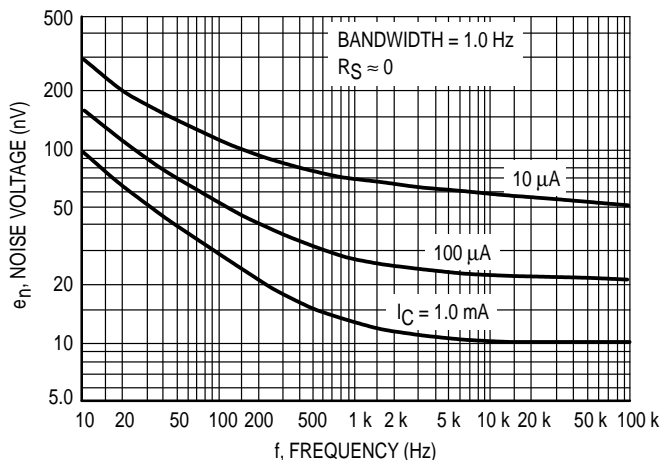


Figure 2. Noise Voltage

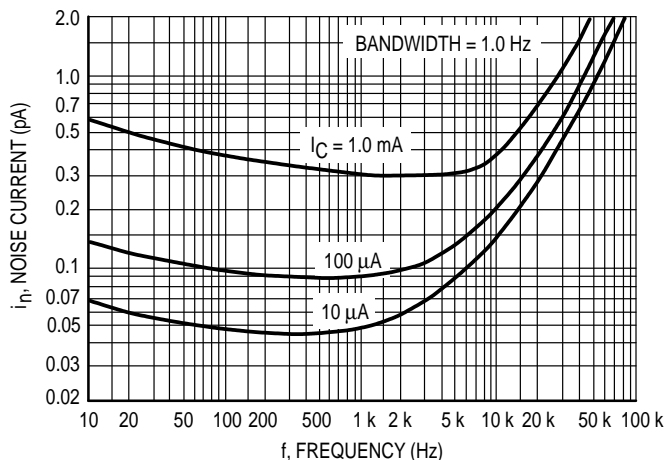


Figure 3. Noise Current

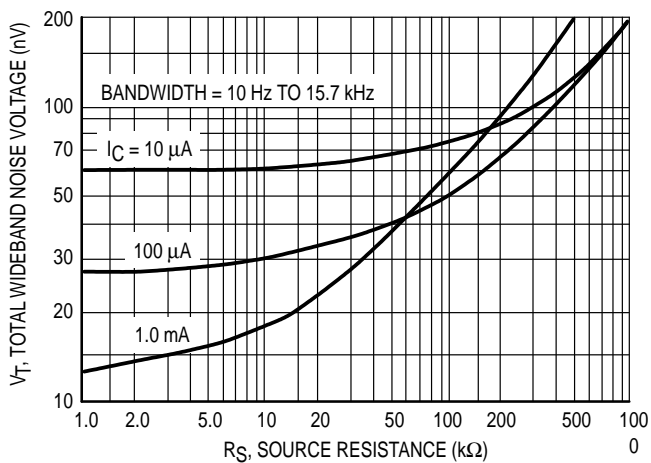


Figure 4. Total Wideband Noise Voltage

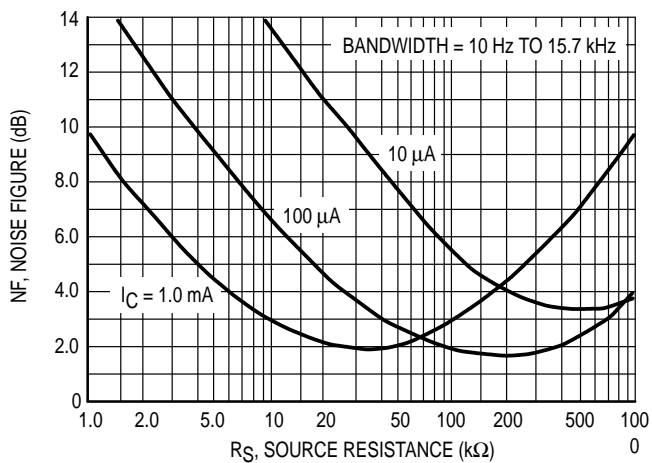


Figure 5. Wideband Noise Figure

SMALL-SIGNAL CHARACTERISTICS

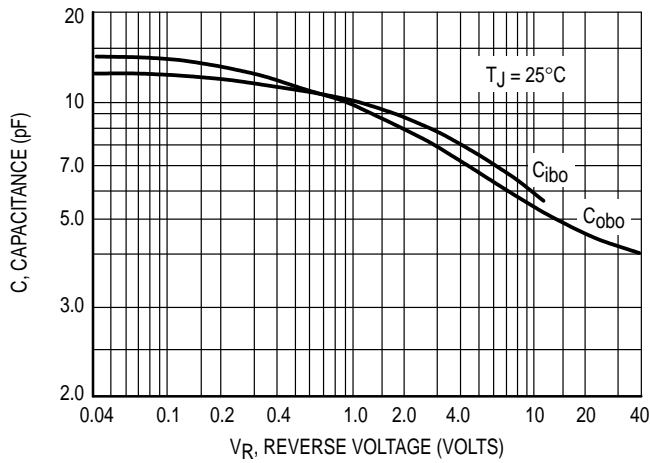


Figure 6. Capacitance

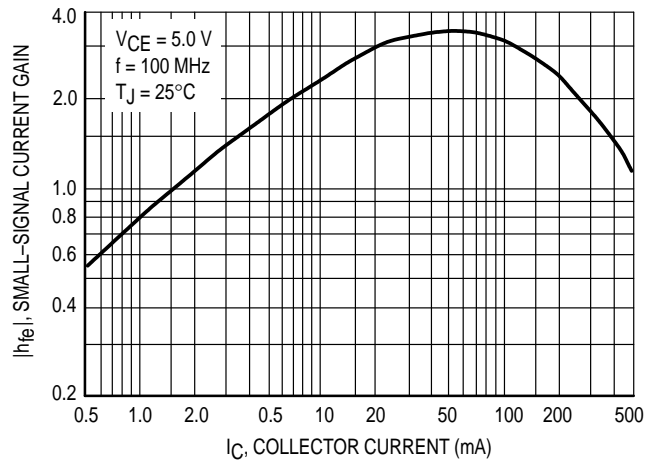


Figure 7. High Frequency Current Gain

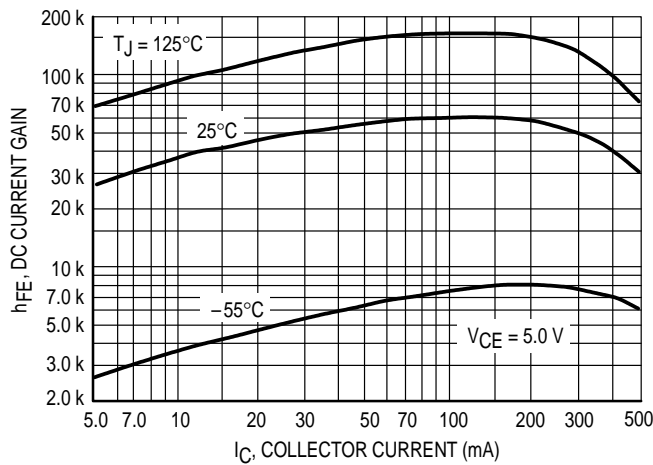


Figure 8. DC Current Gain

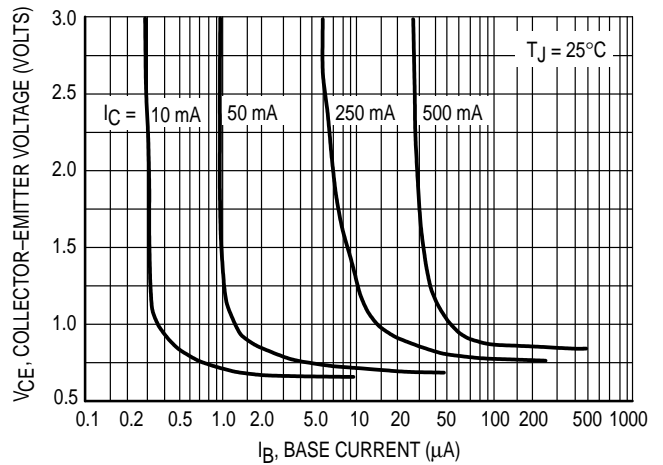


Figure 9. Collector Saturation Region

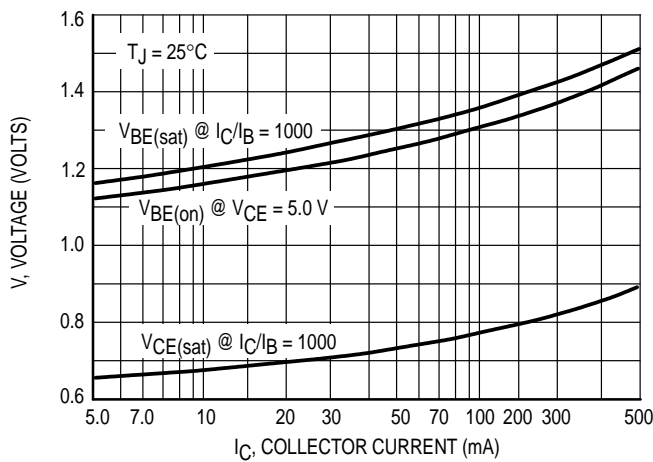


Figure 10. "On" Voltages

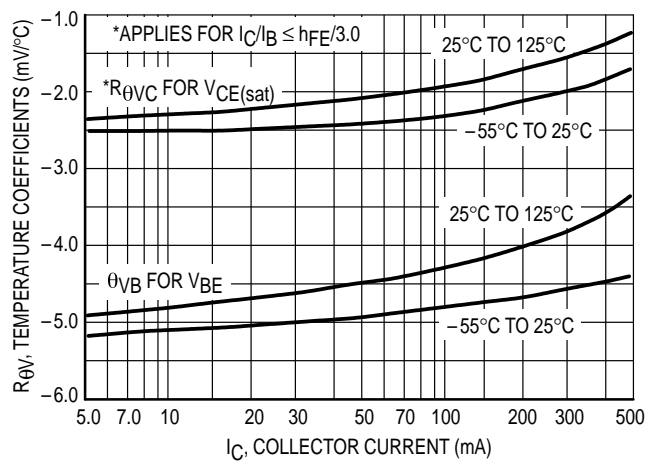


Figure 11. Temperature Coefficients

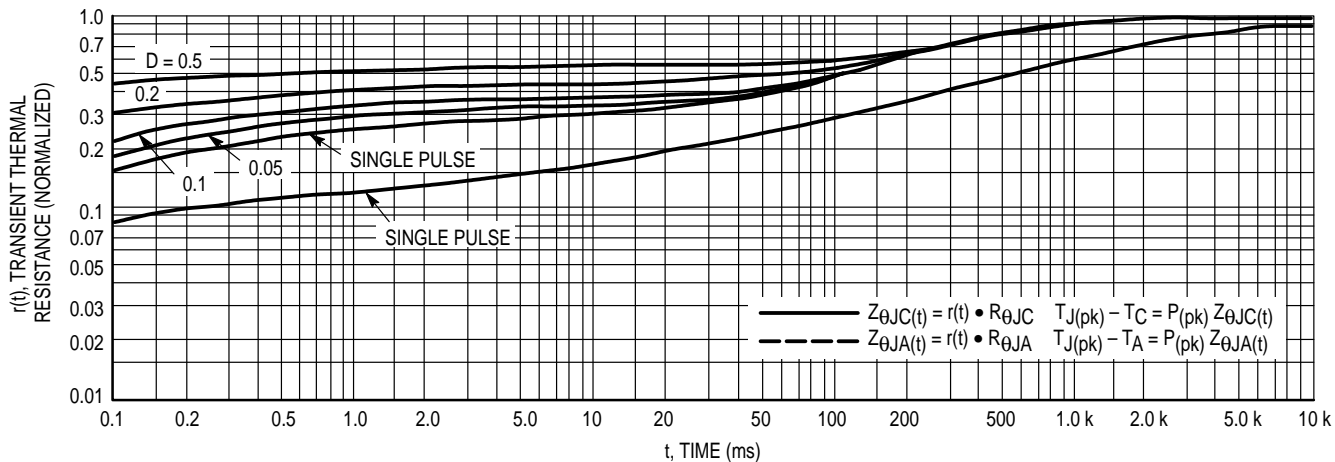


Figure 12. Thermal Response

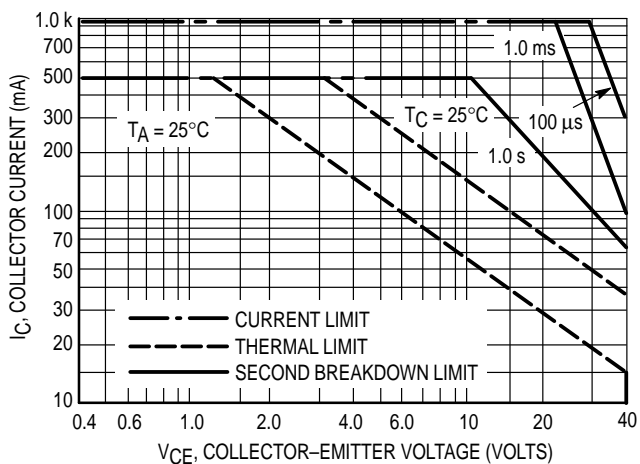
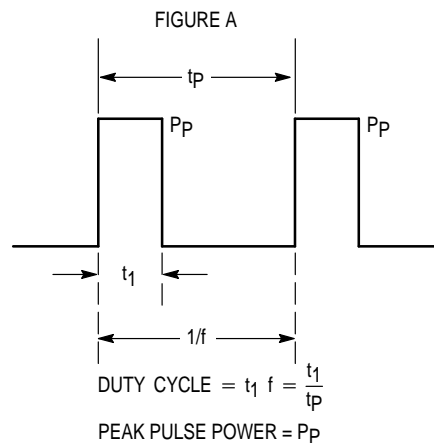
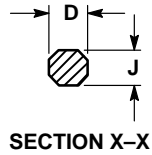
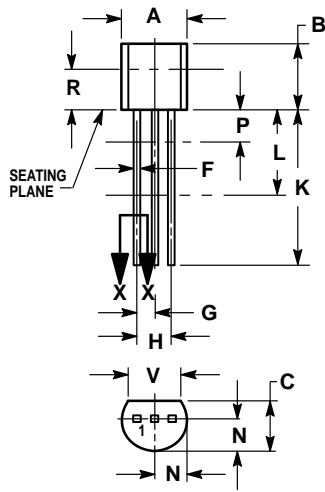


Figure 13. Active Region Safe Operating Area



Design Note: Use of Transient Thermal Resistance Data

PACKAGE DIMENSIONS



**CASE 029-04
(TO-226AA)
ISSUE AD**

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K. MINIMUM LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	—	12.70	—
L	0.250	—	6.35	—
N	0.080	0.105	2.04	2.66
P	—	0.100	—	2.54
R	0.115	—	2.93	—
V	0.135	—	3.43	—

STYLE 17:

- PIN 1. COLLECTOR
2. BASE
3. EMITTER

